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3/17/03

**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

**PATENT**

In re application of: O'DONNELL

Attorney Docket No.:  
LAM1P133/P0582

Application No.: 09/472,757

Examiner: UMEZ ERONINI, *Rachelle T.*

Filed: December 27, 1999

Group: 1765

**Title: INSITU POST ETCH PROCESS TO  
REMOVE REMAINING PHOTORESIST AND  
RESIDUAL SIDEWALL PASSIVATION**

**RECEIVED**  
MAR 10 2003  
TC 1700

**CERTIFICATE OF MAILING**

I hereby certify that this correspondence is being deposited with the United States Postal Service as First Class Mail to: Box AF, Commissioner for Patents, Washington, D.C. 20231 on February 27, 2003.

Signed: *Sue Funchess*  
Sue Funchess

**AMENDMENT D**

*E/A*  
*L. T. M-E.*  
4/23/2003

Box AF  
Commissioner for Patents  
Washington, D.C. 20231

Dear Madame:

This is in response to the Final Office Action mailed January 2, 2003. Please consider the following remarks and amend the above-identified patent application as follows:

**In the Claims:**

Please cancel claim 20 and amend claims 1, 15, 17, and 19, as follows:

1. (Once Amended) A method for etching at least partially through a metal-containing layer disposed above a substrate, wherein part of said metal-containing layer is disposed below an etch mask and part of said metal-containing layer is not disposed below the etch mask, comprising the steps of:

placing the substrate in an etch chamber;

flowing an etchant gas into the etch chamber;